

P1 as $V_{DS} = 5V > V_{GS} - V_T$, the transistor is in saturation region

$$\begin{aligned} I_x = I_D &= \frac{\mu_{Cox} W}{2L} (V_{GS} - V_T)^2 (1 + \lambda V_{DS}) \\ &= 1 \times 10^{-4} \cdot 20 \cdot (1.5)^2 (1 + 0.01 \cdot 5) \\ &= 4.725 \text{ mA} \end{aligned}$$

P2.

$$R_{FET} = \frac{1}{V_{GS} - V_T} \left(\frac{L}{\mu_{Cox} W} \right) = \frac{6}{3 \cdot 1 \times 10^{-4} \cdot 10} = 2 \text{ k}\Omega$$

$$A_v = 1 + \frac{50 \text{ k}}{2 \text{ k}} = 26$$

P3. assume M_2 is in saturation.

$$\begin{cases} I_D = \frac{\mu_{Cox} W}{2L} (V_{GS} - V_T)^2 \\ I_D = \frac{5 - V_{out}}{R} \end{cases}$$

$$\therefore 1 \times 10^{-4} \cdot 5 \cdot 1^2 = \frac{5 - V_{out}}{5 \text{ k}} \Rightarrow \underline{V_{out} = 2.5 \text{ V}}$$

$V_{out} - 0 = V_{DS} > V_{GS} - 1$, confirm assumption

P4 diameter of a 24ga Copper wire. Cross section. = 0.02 in
= 254 μ m

$$\# \text{ of transistors} = \frac{\pi \cdot (\frac{d}{2})^2}{WL} \approx 10^8 \text{ gates}$$

P5 $V_{DS} < V_{GS} - V_T$ in triode region

$$I_D = \frac{\mu C_{ox} W}{L} \left(V_{GS} - V_T - \frac{V_{DS}}{2} \right) V_{DS}$$

$$= 10^{-4} \left(5 - 1 - \frac{2}{2} \right) \cdot 2 \cdot \left(\frac{W}{L} \right)$$

$$= 6 \times 10^{-4} \frac{W}{L}$$

$$= 20 \text{ mA}$$

$$\therefore \frac{W}{L} = \frac{100}{3}$$

e.g. $W = 100 \mu$
 $L = 3 \mu$

P6 $V_{DS} = V_{out} < V_{GS} - V_T$ in triode region

$$I_D = \frac{\mu C_{ox} W}{L} \left(V_{GS} - V_T - \frac{V_{DS}}{2} \right) V_{DS}$$

$$= 2.5 \times 10^{-4} \frac{W}{L}$$

$$I_D = \frac{5 - V_{out}}{20k} = \frac{4}{20k} = 0.2 \text{ mA}$$

$$\Rightarrow \frac{W}{L} = 0.8$$

e.g. $W = 8 \mu$
 $L = 10 \mu$

• 2.

P7. When $V_{GS} > V_T$

$$R_{FET} = \frac{1}{V_{GS} - V_T} \left(\frac{L}{\mu C_{ox} W} \right) = \frac{250}{V_{GS} - 0.5}$$

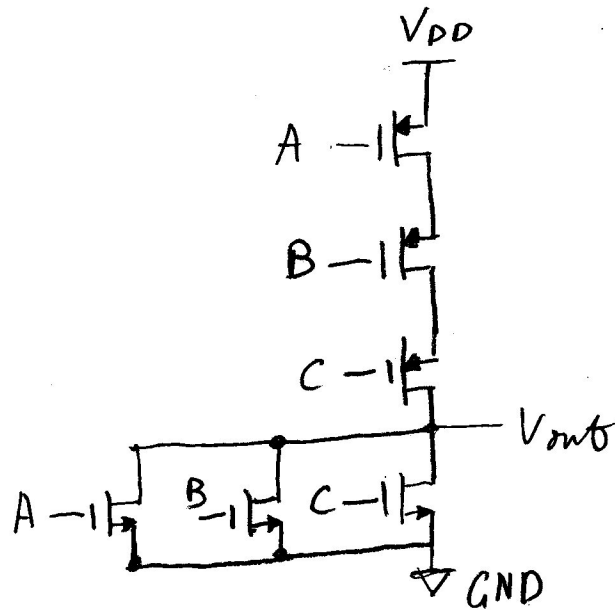


is closed when $V_{GS} > V_T$
is open when $V_{GS} < V_T$

P8 Xor Gate

A	B	C	V_{out}
0	0	0	1
all the other cases			0

$$V_{out} = \overline{(A \cdot B \cdot C)} = \begin{cases} 1 & \text{if } A=B=C=0 \\ 0 & \text{o.w.} \end{cases}$$



P9. ① $V_{GS} = 3.5V$
 $V_{DS} = 8V$ read from the figure $\Rightarrow I_X \approx 3.5mA$

② Saturation

③ $I_X = 3mA$ in triode region

P10 Apparently $\lambda \neq 0$ and it's very small
 \Rightarrow using points from saturation could introduce large error

so, selecting 2 points from triode region

e.g. $I_{D1} = 1mA$, $V_{DS1} = 1V$, $V_{GS1} = 2.5V$

$I_{D2} = 2mA$, $V_{DS2} = 1V$, $V_{GS2} = 3.5V$

$$\therefore I_D = \frac{\mu C_{ox} W}{L} \left(V_{GS} - V_T - \frac{V_{DS}}{2} \right) V_{DS}$$

$$\therefore \frac{I_{D2}}{I_{D1}} = \frac{2}{1} = \frac{(3.5 - 0.5 - V_T)}{(2.5 - 0.5 - V_T)} \Rightarrow V_T = 1V$$

$$\therefore 2 \times 10^{-3} = \mu C_{ox} \cdot \frac{20}{4} \cdot 2 \Rightarrow \mu C_{ox} = 2 \times 10^{-4} A/V^2$$

P11 (a) $V_{GS} = V_{DS} = 3 \quad \therefore V_{DS} > V_{GS} - V_T$ in saturation.

$$I_D = \frac{\mu C_{ox} W}{2L} (V_{GS} - V_T)^2 = 5 \times 10^{-4} \cdot 2^2 = 2 \text{ mA}$$

$$\therefore V_{out} = 3 + I_D \cdot R = 3 + 8 = 11 \text{ V}$$

(b) $V_{DS} = 2 < V_{GS} - V_T$ triode

$$I_D = \frac{\mu C_{ox} W}{L} \left(V_{GS} - 1 - \frac{V_{DS}}{2} \right) V_{DS}$$
$$= \frac{1 \times 10^{-4}}{2} \cdot (4 - 2) \cdot 2 = 0.2 \text{ mA}$$

$$\therefore V_{out} = 2 + R \cdot I_D = 2 + 6 = 8 \text{ V}$$

(c) $V_{DS} = 4 > V_{GS} - V_T$ saturation

$$I_D = 0.5 \text{ mA}$$

$$V_{out} = 4 + I_D \cdot R = 4 + 5 = 9 \text{ V}$$

(d) $V_{GS} < V_T \quad I_D = 0$

$$\therefore V_{out} = 4 \text{ V}$$